

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	337	(pressure pressured pressurize pressurized pressurizable) and (clean adj room) and partition with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:44
L10	14	(pressure pressured pressurize pressurized pressurizable) and (clean adj room) and partition with chamber with contaminat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:46
L11	24	(pressure pressured pressurize pressurized pressurizable) and (clean adj room) and partition with chamber same contaminat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:58
L12	10	L11 not l10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:59
L13	227	(pressure pressured pressurize pressurized pressurizable) and (clean adj room) and partition with chamber and contaminat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:58
L14	4	(clean adj room) and (pressure pressured pressurize pressurized pressurizable) same partition same chamber same contaminat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:59
L15	247	(pressure pressured pressurize pressurized pressurizable) same partition same chamber same contaminat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 12:00
L16	9	(pressure pressured pressurize pressurized pressurizable) same partition same chamber same contaminat\$5 and ("204" "205").clas.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 12:00
L17	44	(pressure pressured pressurize pressurized pressurizable) same partition same chamber same contaminat\$5 and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 12:05

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L18	753	(pressure pressured pressurize pressurized pressurizable) same wall same chamber same contaminat\$5 and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 13:00
L19	155	(pressure pressured pressurize pressurized pressurizable) same wall same chamber same contaminat\$5 and (semiconductor wafer) and ("204" "205" "134" "15" "451").clas.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 13:01
L20	98	("4924890").URPN.	USPAT	OR	ON	2006/09/13 13:29
L21	245	electroless with plating with pretreatment	USPAT	OR	ON	2006/09/13 13:29
L22	67	electroless with plating with pretreatment and (semiconductor wafer)	USPAT	OR	ON	2006/09/13 13:41
L23	1166	electroless with plating and (semiconductor wafer) and (CMP chemical adj mechanical adj polish\$3)	USPAT	OR	ON	2006/09/13 13:34
L24	75	electroless with plating and (semiconductor wafer) and (CMP chemical adj mechanical adj polish\$3) and "427".clas.	USPAT	OR	ON	2006/09/13 13:34
L25	186	electroless with plating with activation and (semiconductor wafer)	USPAT	OR	ON	2006/09/13 13:41
L26	164	electroless with plating with activation and (semiconductor wafer) and copper	USPAT	OR	ON	2006/09/13 13:42
L27	16	electroless with plating with activation and (semiconductor wafer) and copper.ti.	USPAT	OR	ON	2006/09/13 13:42
L28	33	electroless with plating with activation and (semiconductor wafer) and copper.ab.	USPAT	OR	ON	2006/09/13 13:46
L29	145	"15".clas. and (pencil roller) same (semiconductor wafer)	USPAT	OR	ON	2006/09/13 13:47
L30	6	"15".clas. and (pencil) same (semiconductor wafer)	USPAT	OR	ON	2006/09/13 13:47
L31	140	"15".clas. and (roller) same (semiconductor wafer)	USPAT	OR	ON	2006/09/13 13:47

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S4	63	concentration with (analyz\$3 determin\$3 assay\$3) with (copper) with (ion) and (electroplat\$ plat\$4) and ("204" "205").clas.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 16:00
S8	67	concentration with (analyz\$3 determin\$3 assay\$3) with (copper) with (ion) and (electroplat\$ plat\$4) and ("204" "205").clas.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 16:01
S7	87	concentration with (analyz\$3 determin\$3 assay\$3) with (copper) with (ion) and (electroplat\$ plat\$4) and ("204" "205" "427" "118").clas.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 16:01
S15	3	("6294059" "6929722").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/12 16:03
S14	15	S13 and partition with chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/13 11:44